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033035 M 0342

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Kensaku MOTOKI, et al.

U.S. Serial No.: 10/691,569

Group Art Unit: 2814

Filed: October 24, 2003

Examiner: Marcos D. Pizarro Crespo

For: GaN Single Crystal Substrate and Method of Making the Same

FOURTH INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:


Pursuant to the duty of disclosure under 37 C.F.R. § 1.56, Applicants enclose an Information Disclosure Citation Form (PTO-1449) and a copy of the document cited therein. The document was cited by the Examiner in copending application no. 10/691,540.

It is respectfully requested that the cited document be considered by the Examiner, that they be made officially of record therein, and that the document be listed on the face of any patent which may issue from this application. An Official Action on the merits has issued for this application. In accordance with the requirements of 37 C.F.R. §1.97(c), Applicants attach a check which includes payment of the \$180 requisite fee (37 C.F.R. §1.17(p)).

Respectfully submitted,

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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET 033035 M 0342	SERIAL NO. 10/691,569
	APPLICANT: Kensaku MOTOKI, et al.	
	FILING DATE October 24, 2003	GROUP ART UNIT 2814

U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE, IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION YES NO	
	AL							
	AM							
	AN							
	AO							
	AP							

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

AQ	Nam et al. "Growth of GaN and Al _{0.8} Ga _{0.2} N on Patterned Substrates via Organometallic Vapor Phase Epitaxy" Jpn.j. Appl. Phys. Vol 36 (May 1, 1997), Pt. 2, No. 5A, pg. L532
AR	
AS	
EXAMINER:	DATE CONSIDERED:
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	